ECEN326: Electronic Circuits Spring 2022

Lecture 8: Output Stages and Power Amplifiers



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Announcements

- Homework 8 due Apr 28
- Exam 3 May 5
 - 12:30 2:30
 - Closed book w/ one standard note sheet
 - 8.5"x11" front & back
 - Bring your calculator
 - Emphasis will be on Lectures 7-8
 - Sample Exam3s posted on website
- Reading
 - Razavi Chapter 14

Agenda

- General Output Stage Considerations
- Emitter Follower as a Power Amplifier
- Push-Pull Stage
- Improved Push-Pull Stage
- Large-Signal Considerations
- Heat Dissipation
- Efficiency and Power Amplifier Classes

Why Special Output Stages or Power Amplifiers?

 Power amplifiers are necessary to efficiently drive a load with high power

- Examples
 - A cellphone may need 1W of power at the antenna
 - Audio systems require tens to hundreds of Watts
- As ordinary voltage/current amplifiers are not suited for efficiently supporting these power levels, specialized output stages are necessary

Power Amplifier Characteristics

- Can drive a small "heavy" load resistance
 - Example: Speaker resistance can be $4-16\Omega$
- Delivers large current levels
 - Often in the hundreds of mA
- Requires large voltage swings
- Draws a large amount of power from the supplies
- Dissipates a large amount of power, and thus can get hot

Example: Delivering 1W to an 8Ω speaker

Sinusoidal
$$P_{out} = \left(\frac{V_P}{\sqrt{2}}\right)^2 \cdot \frac{1}{R_L} = 1W$$

This results in a peak voltage

$$V_P = 4V$$

and a peak current

$$I_P = \frac{V_P}{R_L} = \frac{4V}{8\Omega} = 500 mA$$

Power Amplifier Performance Metrics

- Linearity or Distortion
 - Audio amplifiers must have low distortion to reproduce music with high fidelity
- Power Efficiency

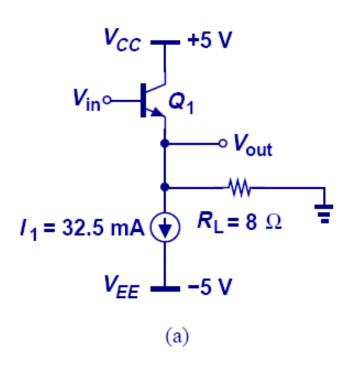
$$\eta = \frac{\text{Power Delivered to Load}}{\text{Power Drawn from Supply}}$$

- Maximum Voltage Rating
 - May require high power supplies
 - Transistors must have sufficiently high breakdown voltages

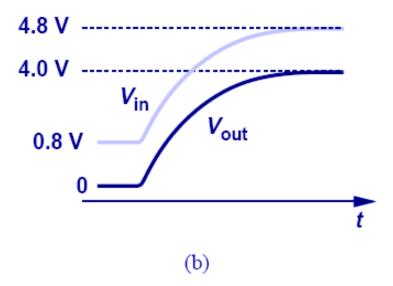
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Emitter Follower Large-Signal Behavior: Positive Half-Cycle

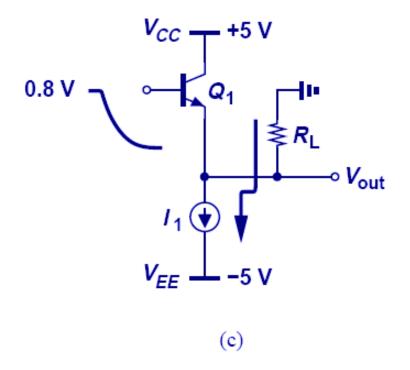


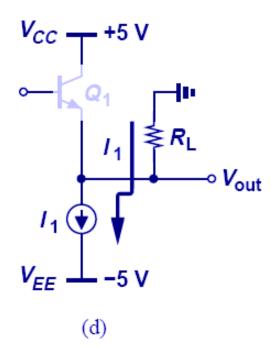
Here V_{BE} is assumed to be 0.8V due to the high current levels



- As V_{in} increases V_{out} also follows and Q₁ provides more current
- No major issue with the input signal positive half-cycle

Emitter Follower Large-Signal Behavior: Negative Half-Cycle

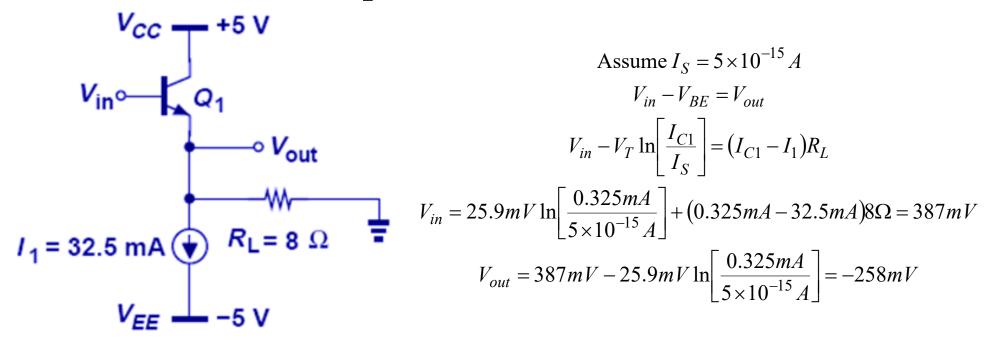




- However as V_{in} decreases, V_{out} also decreases, shutting off Q₁ and resulting in a constant V_{out}
- The output signal clips at a minimum value of –I₁R₁

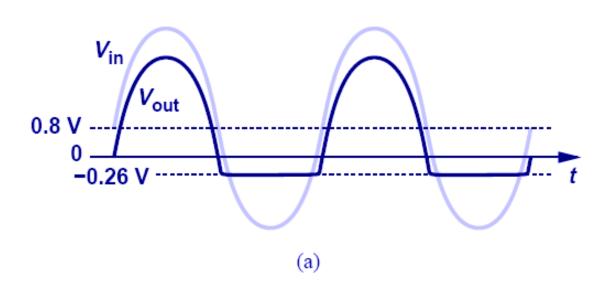
Example: Emitter Follower

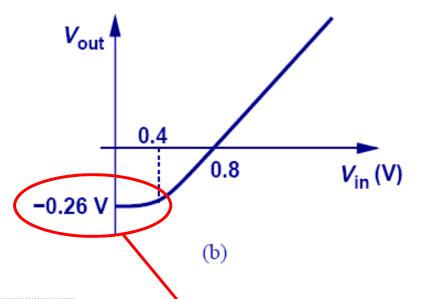
What are the input and output voltages when I_{C1} drops to 1% of I₁?



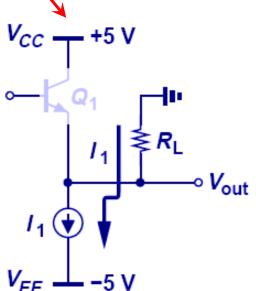
- At this current level, the V_{BE} has dropped to 645mV
- For voltage levels much below 400mV, the output will saturate at $-I_1R_1 = -260$ mV

Linearity of an Emitter Follower





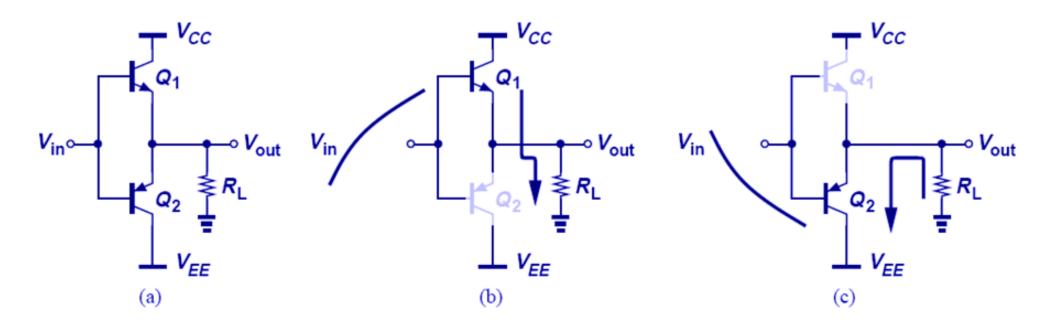
- As Vin decreases the output waveform will be clipped, introducing nonlinearity in I/O characteristics
- ➤ Overall, the fixed I₁ limits the output swing



Agenda

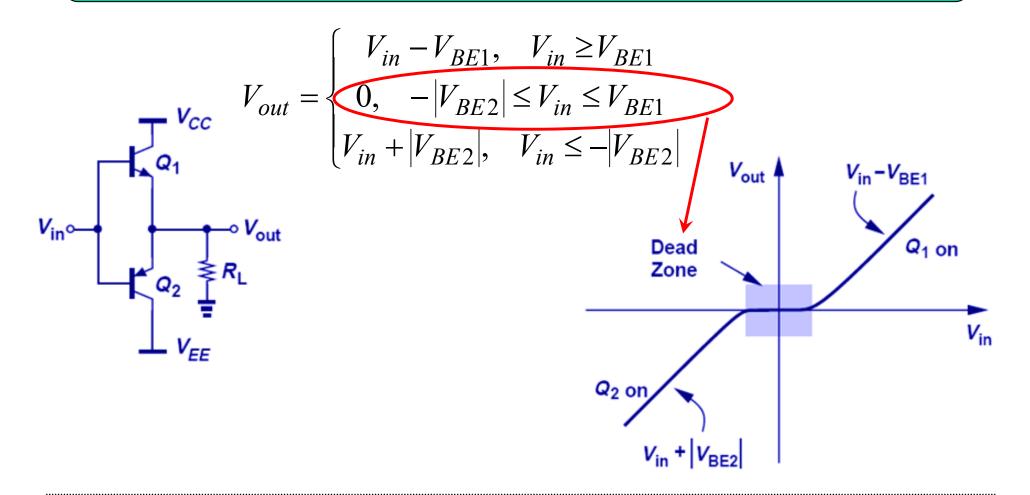
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Push-Pull Stage



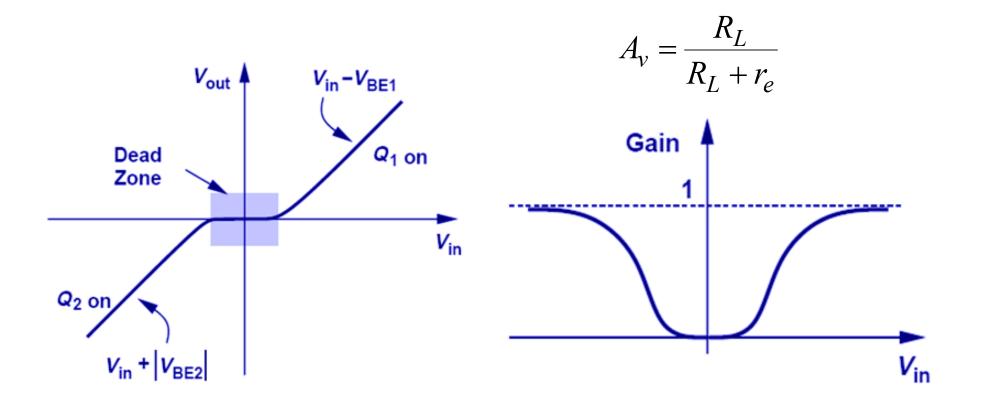
- As V_{in} increases, Q₁ is on and pushes a current into R_L.
- \triangleright As V_{in} decreases, Q_2 is on and pulls a current out of R_L .
- For positive V_{in} , Q_1 shifts the output down and for negative V_{in} , Q_2 shifts the output up.

Overall I/O Characteristics of Push-Pull Stage



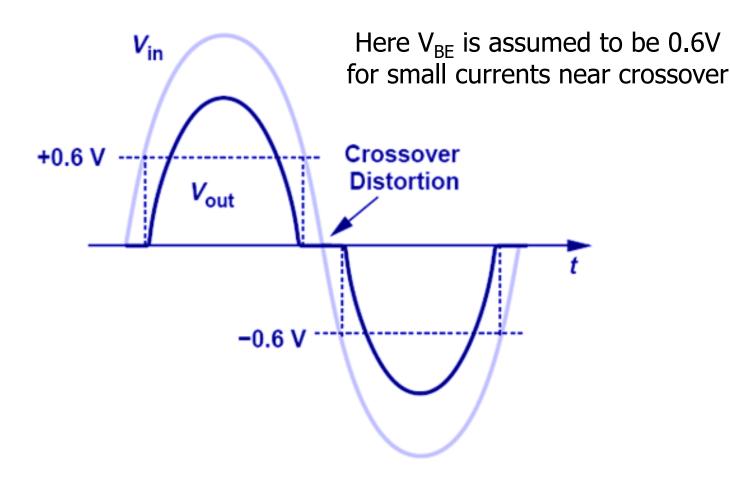
- ightharpoonup However, for small V_{in} , there is a dead zone (both Q_1 and Q_2 are off) in the I/O characteristic, resulting in gross nonlinearity
- The dead zone is from -|V_{BE2}| ≤ V_{in} ≤ V_{BE1}

Small-Signal Gain of Push-Pull Stage



- The push-pull stage exhibits a gain that tends to unity when either Q1 or Q2 is on.
- When Vin is very small, the gain drops to zero.

Sinusoidal Response of Push-Pull Stage



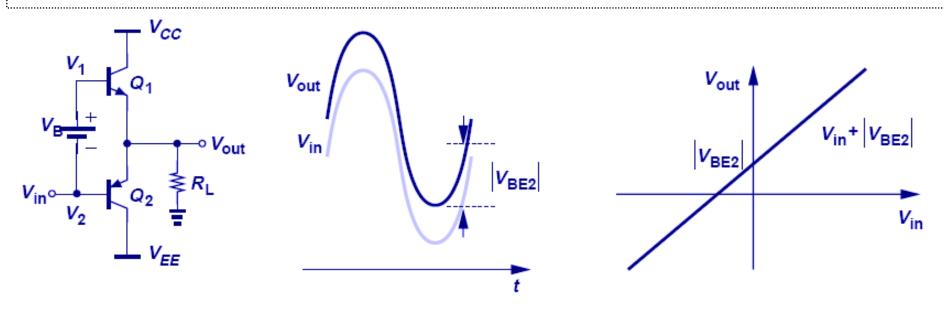
For large Vin, the output follows the input with a fixed DC offset, however as Vin becomes small the output drops to zero and causes "Crossover Distortion."

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Improved Push-Pull Stage

With a battery of V_B inserted between the bases of Q_1 and Q_2 , the dead zone is eliminated.



What should V_B be so that at least one transistor is always on?

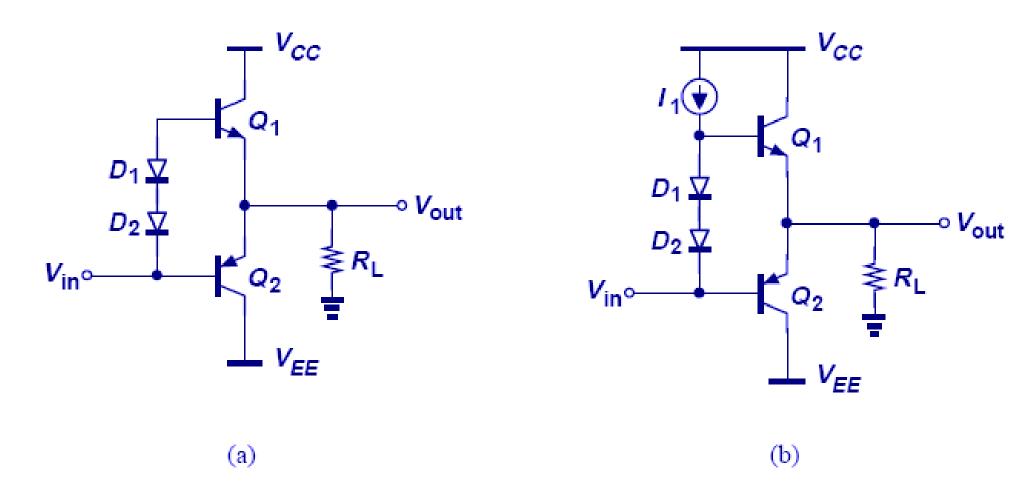
$$Q_2$$
 turns off when $V_{in} = -|V_{BE2}|$

at this point we want Q_1 on, or $V_1 = V_{BE1}$

Thus,
$$V_B = V_1 - V_{in} = V_{BE1} - (-|V_{BE2}|)$$

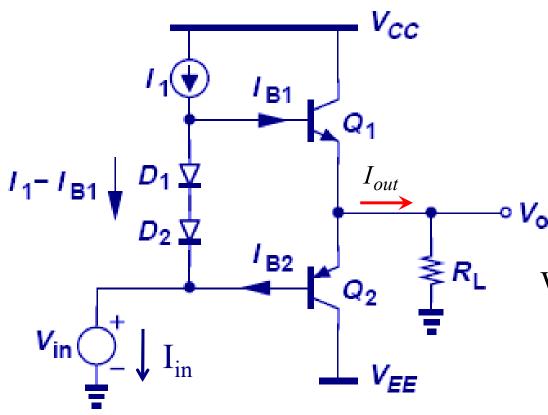
$$V_B = V_{BE1} + \left| V_{BE2} \right|$$

Implementation of V_B



- Since V_B=V_{BE1}+|V_{BE2}|, a natural choice would be two series diodes
- \triangleright I₁ in figure (b) is used to bias the diodes and Q₁.

Example: Current Flow I



The V_{in} source must support I_1 and the Q_1 and Q_2 base current difference, which can excessively load the source

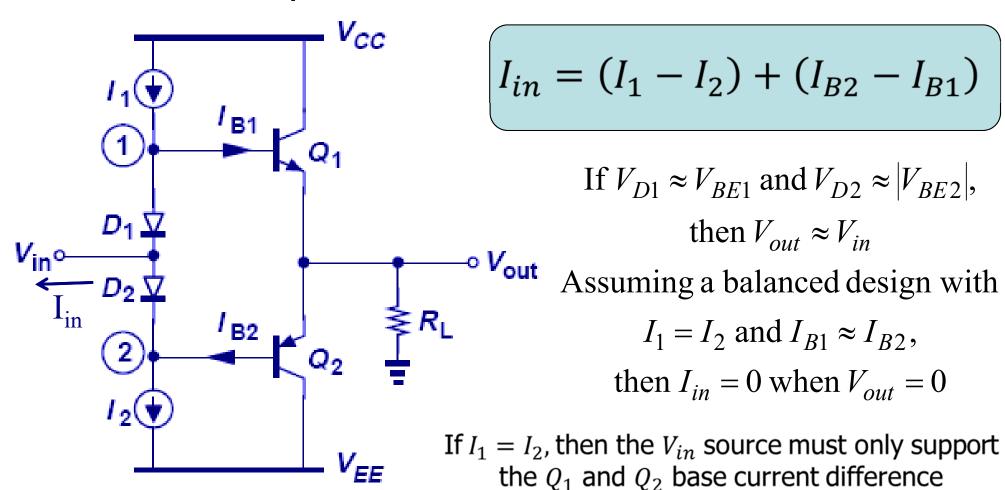
$$I_{in} = I_1 - I_{B1} + I_{B2}$$

When is $I_{in} = I_1$, assuming $\beta_1 = \beta_2$? This occurs when $I_{B1} = I_{B2}$, which implies that $I_{C1} = I_{C2}$ and that $I_{out} = 0$ Thus, this occurs when

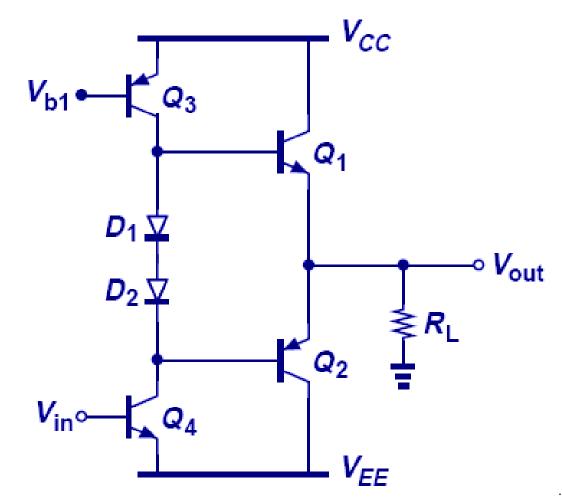
 $V_{out} = 0$

Example: Current Flow II

 The offset between input and output is minimized when the input is in the middle of the diodes



Addition of CE Stage



- \triangleright A CE stage (Q₄) is added to provide voltage gain from the input to the bases of Q₁ and Q₂
- This push-pull circuit is often used in high-power output stages

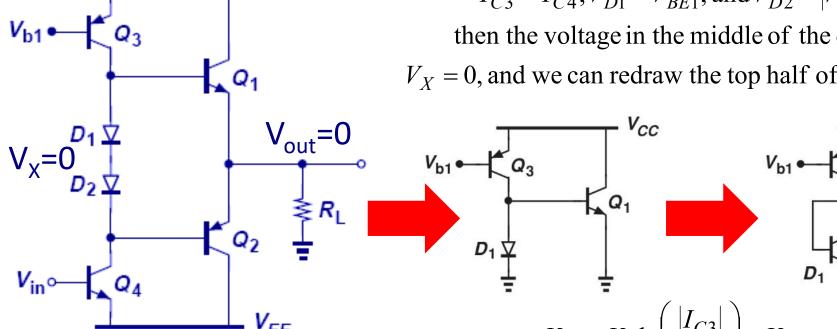
Bias Point Analysis

With $V_{out} = 0$ and assuming that

$$I_{C3} = I_{C4}, V_{D1} = V_{BE1}, \text{ and } V_{D2} = |V_{BE2}|$$

then the voltage in the middle of the diodes

 $V_X = 0$, and we can redraw the top half of the circuit



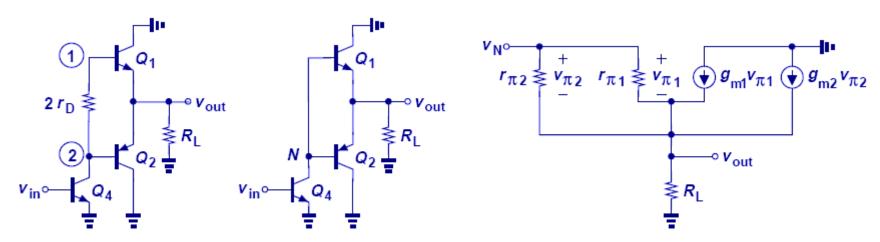
- $V_{D1} = V_T \ln \left(\frac{|I_{C3}|}{I_{S,D1}} \right) = V_{BE1} = V_T \ln \left(\frac{I_{C1}}{I_{S,D1}} \right)$
 - $I_{C1} = \left(\frac{I_{S,Q1}}{I_{S,D1}}\right) I_{C3}$
- For bias point analysis, the circuit can be simplified to the one on the right, which resembles a current mirror
- For a well-defined I_S ratio, D₁ can be realized as a diode-connected transistor

Small-Signal Analysis - I

In order to derive the gain of the circuit, we can treat it as a two-stage amplifier

$$\frac{v_{out}}{v_{in}} = \frac{v_N}{v_{in}} \cdot \frac{v_{out}}{v_N}$$

Assuming $V_A = \infty$ and $r_D = 0$, the second stage can be viewed as 2 parallel emitter followers



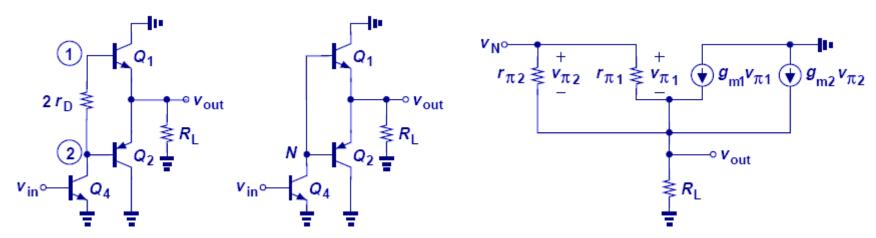
$$\frac{v_{out}}{v_N} = \frac{R_L}{R_L + r_{e1} \| r_{e2}} \approx \frac{R_L}{R_L + \frac{1}{g_{m1} + g_{m2}}}$$

Small-Signal Analysis - II

The gain of the first stage can be expressed as

$$\frac{v_N}{v_{in}} = -g_{m4}R_N \text{ where}$$

$$R_N = r_{\pi 1} || r_{\pi 2} + (g_{m1} + g_{m2})(r_{\pi 1} || r_{\pi 2}) R_L$$



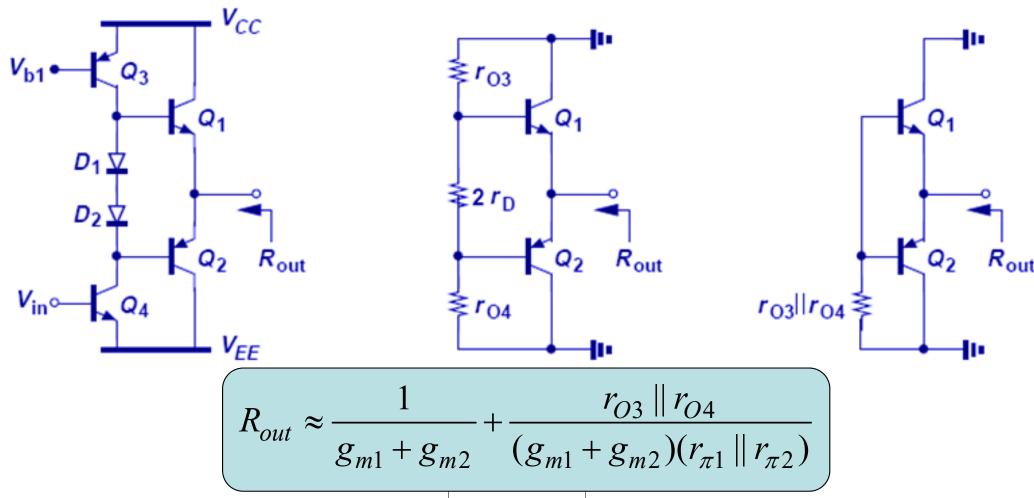
The overall gain is

$$\frac{v_{out}}{v_{in}} = \frac{v_N}{v_{in}} \cdot \frac{v_{out}}{v_N} = -g_{m4} \left[r_{\pi 1} \| r_{\pi 2} + (g_{m1} + g_{m2})(r_{\pi 1} \| r_{\pi 2}) R_L \right] \frac{R_L}{R_L + \frac{1}{g_{m1} + g_{m2}}}$$

 $\frac{v_{out}}{v_{in}} = -g_{m4}(r_{\pi 1}||r_{\pi 2})(g_{m1} + g_{m2})R_L$

Output Resistance Analysis

For the output resistance, we do need to consider the finite r₀ of Q₃ & Q₄

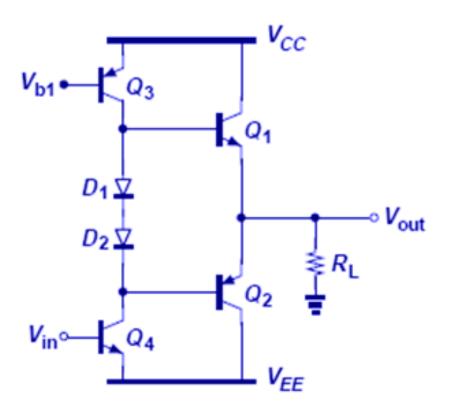


If β is low, the second term of the output resistance will rise, which will be problematic when driving a small resistance.

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Example: Biasing



Design Specs:

Common Emitter $A_v = 5$

Output Stage $A_v = 0.8$

with
$$R_L = 8\Omega$$
, $\beta_{npn} = 2\beta_{pnp} = 100$
and assume $I_{C1} \approx I_{C2}$

1. From the output stage gain and $I_{C1,2}$ conditions we can find $g_{m1,2}$ and $I_{C1,2}$

$$A_{v,OS} = \frac{v_{out}}{v_N} = \frac{R_L}{R_L + \frac{1}{g_{m1} + g_{m2}}} = 0.8$$

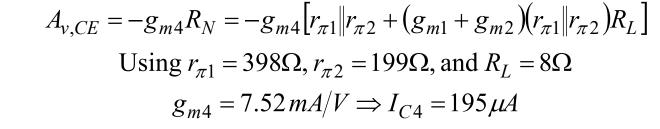
$$g_{m1} + g_{m2} = \frac{1}{2\Omega}$$

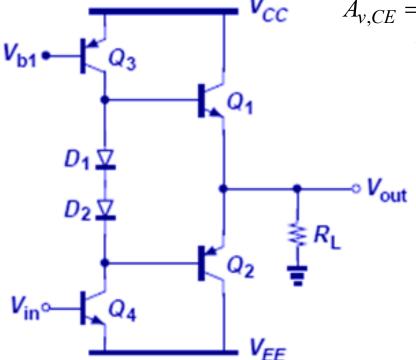
with
$$I_{C1} = I_{C2} \Rightarrow g_{m1} = g_{m2} = \frac{1}{4} (\Omega^{-1}) = 250 \, mA/V$$

and $I_{C1} = I_{C2} = 6.5 \, mA$

Example: Biasing

2. From the Common Emitter gain condition we can find I_{C4}

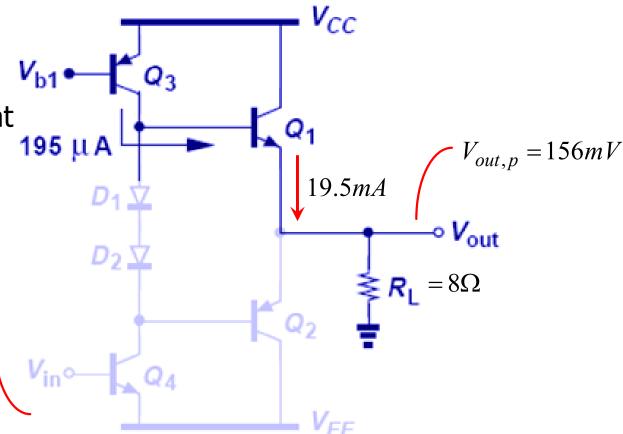




However, this design procedure neglects any output swing specification!

Problem of Base Current

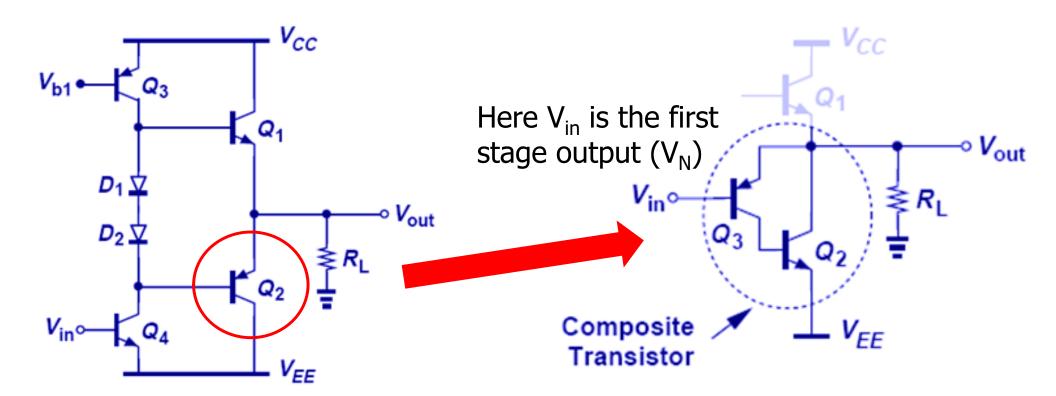
Note, this assumes that I_{C3} is the same as I_{C4} , which may not exactly be the case due to the different $\beta_{1,2}$



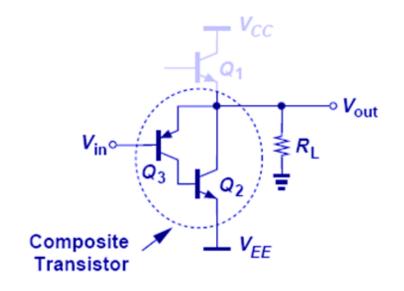
 \triangleright 195 μA of base current in Q₁ can only support 19.5 mA of collector current, insufficient for high current operation (hundreds of mA).

Modification of the PNP Emitter Follower

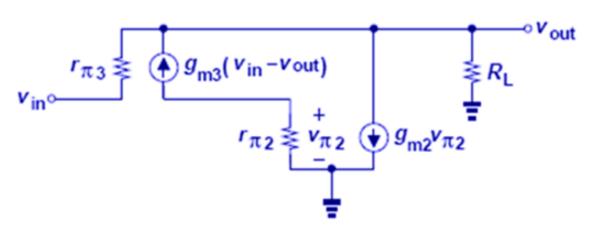
- Another output stage issue is that the Q_2 PNP transistor typically have low current gain (β) and low f_T
- Using a composite transistor consisting of an emitter follower PNP (Q_3) and a common emitter NPN (Q_2) allows for improved performance



Modified PNP Emitter Follower Gain & Output Resistance



Small-Signal Model



Writing a KCL at the output node

$$\frac{v_{out} - v_{in}}{r_{\pi 3}} - g_{m3}(v_{in} - v_{out}) + g_{m2}(-g_{m3})(v_{in} - v_{out})r_{\pi 2} + \frac{v_{out}}{R_L} = 0$$

As the Q_3 collector current forms the Q_2 base current

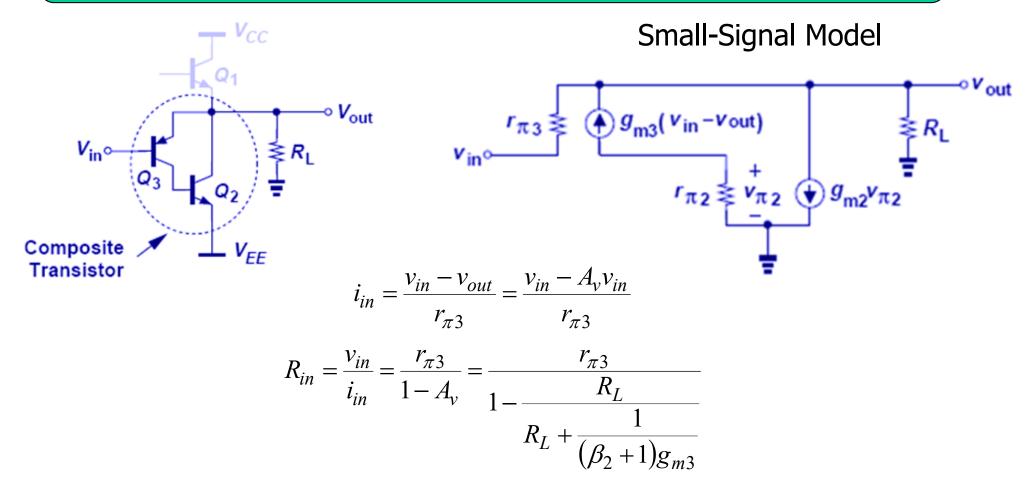
$$g_{m2} = \beta_2 g_{m3}$$

$$\frac{v_{out}}{v_{in}} = \frac{R_L}{R_L + \frac{1}{(\beta_2 + 1)g_{m3} + \frac{1}{r_{\pi 3}}}}$$

$$R_{out} = \frac{1}{(\beta_2 + 1)g_{m3} + \frac{1}{r_{\pi 3}}} \approx \frac{1}{(\beta_2 + 1)g_{m3}}$$

Output resistance has been reduced by β_2 +1 factor 32

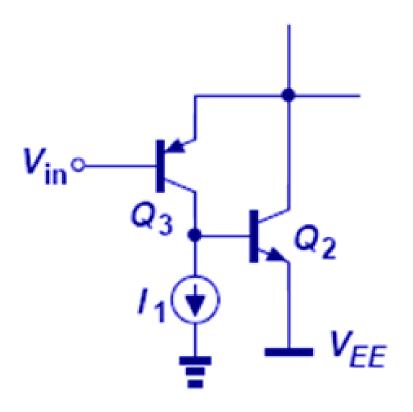
Modified PNP Emitter Follower Input Resistance



$$R_{in} = r_{\pi 3} + \beta_3 (\beta_2 + 1) R_L$$

Input resistance has been increased by $\sim(\beta_2+1)$ factor

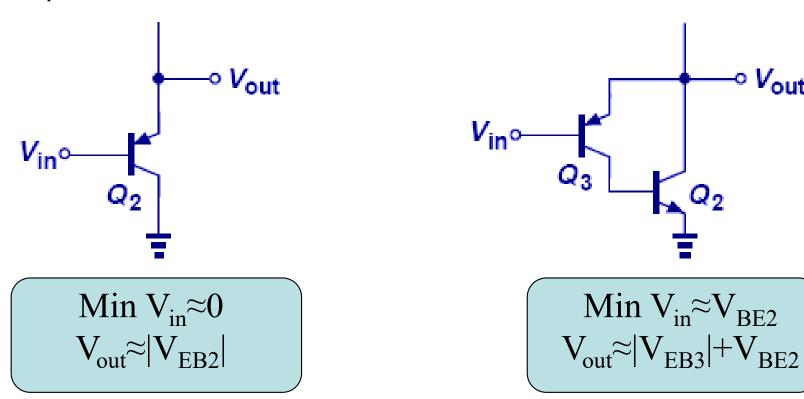
Additional Bias Current



- Q₂ is often a large transistor to support the output current levels, resulting in large base capacitance
- ▶ I₁ is added to the base of Q₂ to provide an additional bias current to Q₃ so the capacitance at the base of Q₂ can be charged/discharged quickly

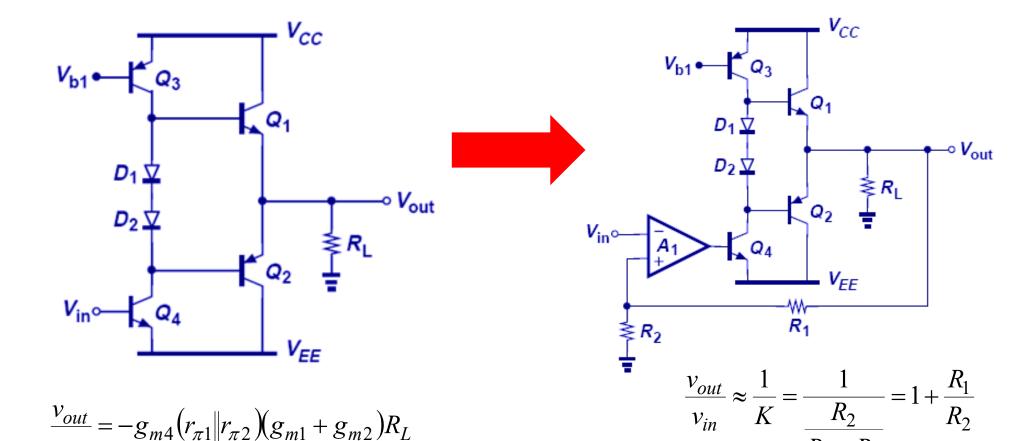
Example: Minimum V_{in}

- There is a minimum Vin for which the effective emitter follower transistors remain in active mode
- Here we conservatively assume for active mode we need a min. V_{BC}=0V
 Simple PNP Emitter Follower
 Modified PNP Emitter Follower



The modified PNP emitter follower has a reduced input range by V_{BE2}

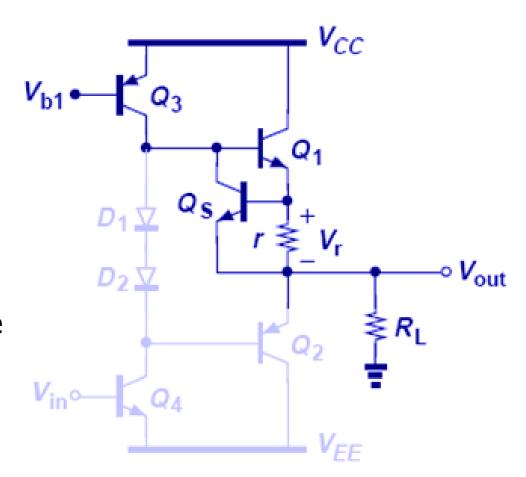
HiFi Design



 As g_{m1} and g_{m2} vary dramatically during large signal operation, the circuit displays nonlinear distortion Placing the output stage in a negative feedback loop allows for a more constant gain, and thus better linearity

Short-Circuit Protection

- Excessive output stage current can result if the output is shorted to ground, damaging the circuit
- Q_s and r are used to "steal" some base current away from Q₁ when the output is accidentally shorted to ground, preventing short-circuit damage
- Drawbacks
 - r increases output resistance
 - Voltage drop across r reduces maximum output swing

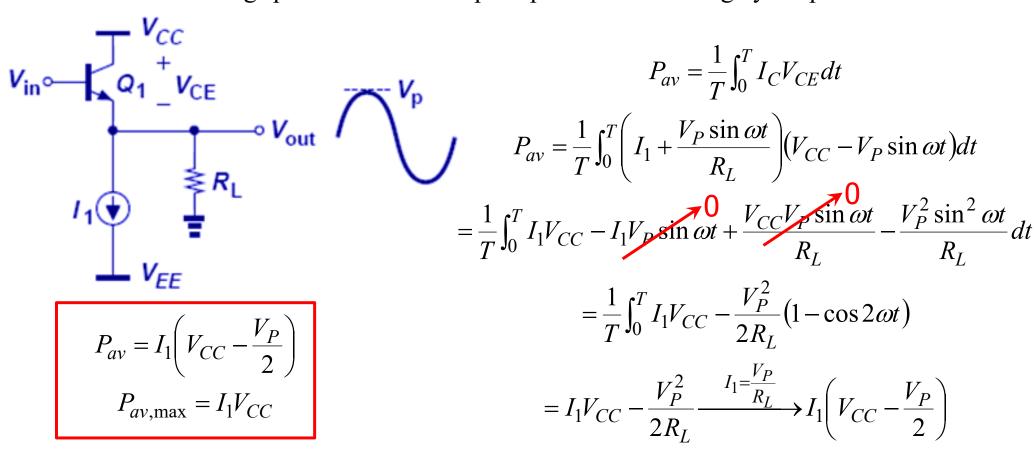


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Emitter Follower Power Rating

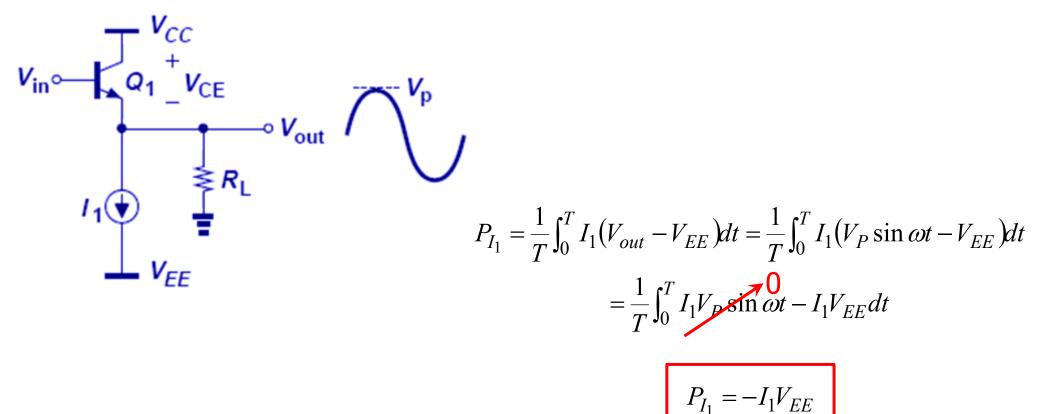
The average power dissipated by Q_1 can be calculated by integrated the current - voltage product over a complete period and dividing by the period time.



➤ Maximum power dissipated across Q₁ occurs in the *absence* of a signal.

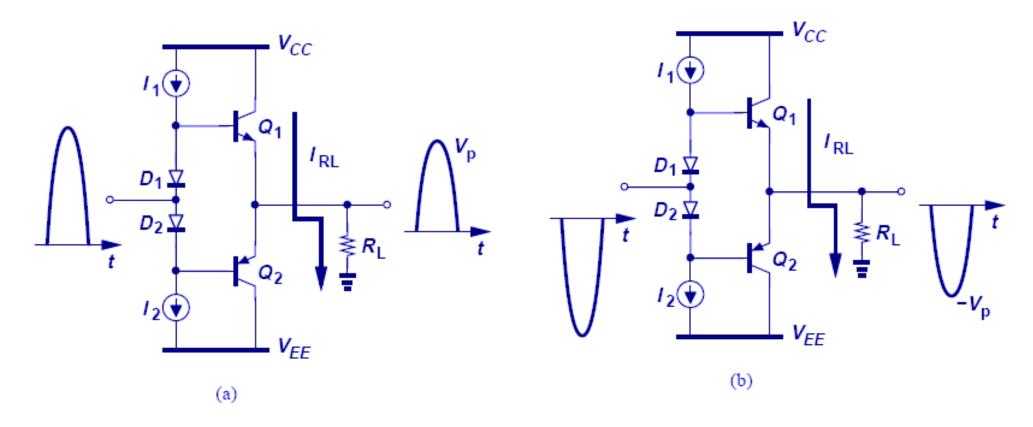
Example: Current Source Power Dissipation

The power dissipated by the I₁ current source is also important, as it will
ultimately need to be realized at the transistor level also



Note that the I₁ power is positive, as V_{FF} is a negative supply

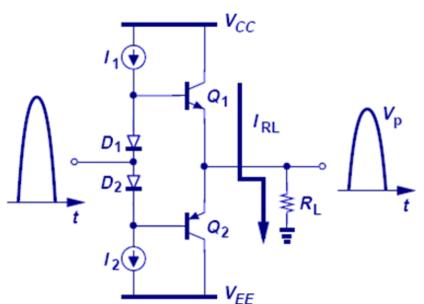
Push-Pull Stage Power Rating



 Assuming a symmetric design, the power ratings of Q1 and Q2 are the same and can be computed by integrating over a half-period.

Push-Pull Stage Power Rating

$$P_{av} = \frac{1}{T} \int_0^{T/2} V_{CE} I_C dt = \frac{1}{T} \int_0^{T/2} \left(V_{CC} - V_P \sin \omega t \right) \left(\frac{V_P}{R_L} \sin \omega t \right) dt$$



$$= \frac{1}{T} \int_{0}^{T/2} \frac{V_{CC}V_{P}}{R_{L}} \sin \omega t - \frac{V_{P}^{2}}{R_{L}} \sin^{2} \omega t dt$$

$$= \frac{1}{T} \int_{0}^{T/2} \frac{V_{CC}V_{P}}{R_{L}} \sin \omega t dt - \frac{1}{T} \int_{0}^{T/2} \frac{V_{P}^{2}}{2R_{L}} (1 - \cos 2\omega t) dt$$

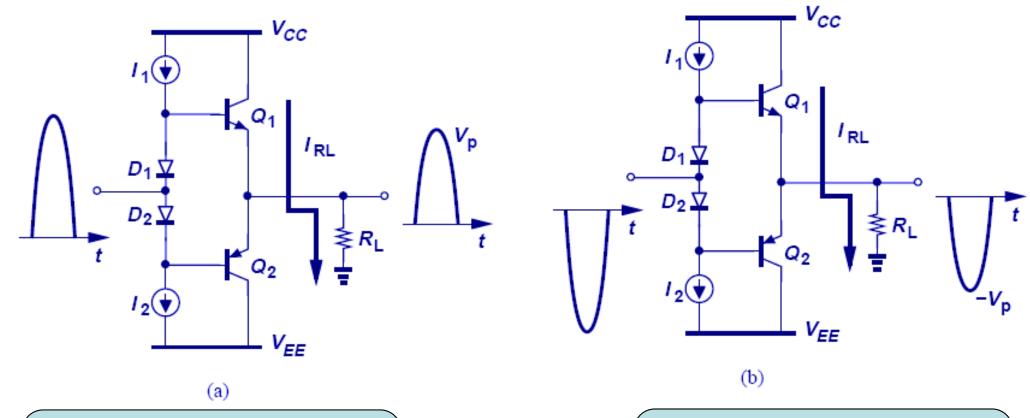
$$= \frac{V_{CC}V_{P}}{\pi R_{L}} - \frac{V_{P}^{2}}{4R_{L}}$$

$$P_{av} = \frac{V_P}{R_L} \left(\frac{V_{CC}}{\pi} - \frac{V_P}{4} \right)$$

Maximum power occurs with
$$V_P = \frac{2V_{CC}}{\pi}$$

$$P_{av,\text{max}} = \frac{V_{CC}^2}{\pi^2 R_L}$$

Example: Push-Pull Pav



$$P_{av} = \frac{V_P}{R_L} \left(\frac{V_{CC}}{\pi} - \frac{V_P}{4} \right)$$

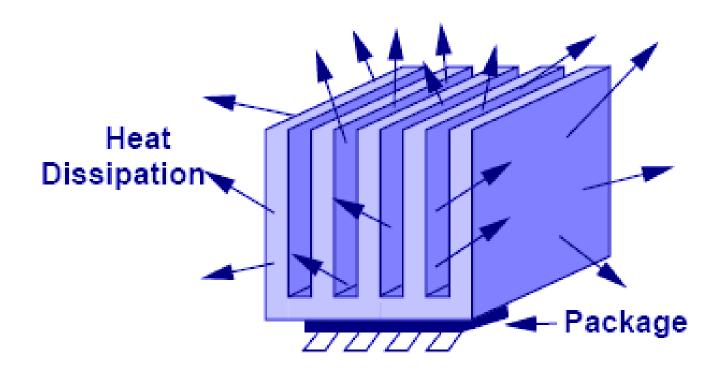




If
$$V_p = 4V_{CC}/\pi \rightarrow P_{av}=0$$

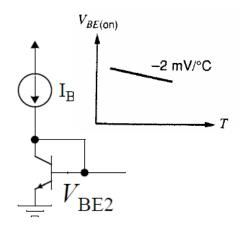
Impossible since V_p cannot go above supply (V_{CC})

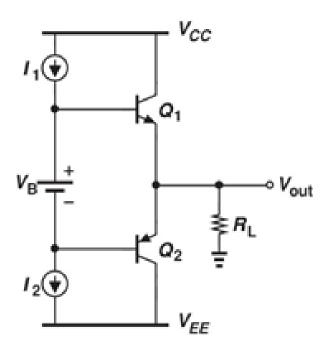
Heat Sink



Heat sink, provides large surface area to dissipate heat from the chip.

Thermal Runaway



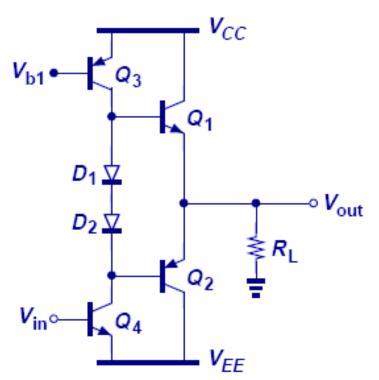


- For a constant I_C, V_{BE} has a negativeto-absolute-temperature (NTAT) coefficient of approximately -2mV/°K
- Conversely, if the push-pull output stage is biased with a constant voltage, the current will increase with temperature
- This increased current results in more heat (higher temperature), and thus more current
- This positive feedback loop is called thermal runaway and can result in transistor damage

Thermal Runaway Mitigation

• Assuming that Q_3 and Q_4 have relatively constant bias currents with temperature (using good current mirror techniques), the diode voltages drop with temperature

Diode Voltages



$$V_{D1} + V_{D2} = V_T \ln \frac{I_{D1}}{I_{S,D1}} + V_T \ln \frac{I_{D2}}{I_{S,D2}} = V_T \ln \frac{I_{D1}I_{D2}}{I_{S,D1}I_{S,D2}}$$

Transistor V_{BE} Voltages

$$V_{BE1} + V_{BE2} = V_T \ln \frac{I_{C1}}{I_{S,Q1}} + V_T \ln \frac{I_{C2}}{I_{S,Q2}} = V_T \ln \frac{I_{C1}I_{C2}}{I_{S,Q1}I_{S,Q2}}$$

From a KVL, these voltage pairs are the same

$$V_T \ln \frac{I_{D1}I_{D2}}{I_{S,D1}I_{S,D2}} = V_T \ln \frac{I_{C1}I_{C2}}{I_{S,Q1}I_{S,Q2}}$$

$$\frac{I_{D1}I_{D2}}{I_{S,D1}I_{S,D2}} = \frac{I_{C1}I_{C2}}{I_{S,Q1}I_{S,Q2}}$$

Using diode biasing prevents thermal runaway since the currents in Q_1 and Q_2 will track those of D_1 and D_2 as long as their I_s 's track with temperature.

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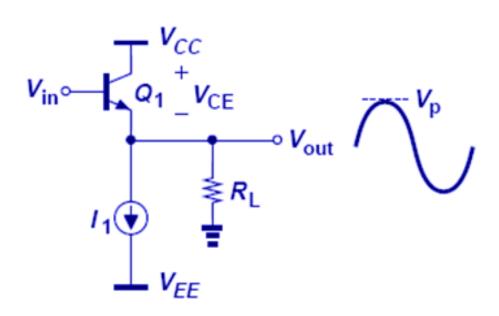
Power Amplifier Efficiency

 Power amplifier efficiency is critical because PAs draw a significant amount of power from the supply voltages

 Power amplifier efficiency is the ratio of the average power delivered to the load over the total power consumed from the supplies

$$\eta = \frac{\text{Power Delivered to Load}}{\text{Power Drawn from Supply}} = \frac{P_{out}}{P_{out} + P_{ckt}}$$

Emitter Follower Efficiency



The average power delivered to the load is

$$P_{out} = \frac{V_P^2}{2R_L}$$

The average power consumed by Q_1 is

$$P_{Q_1} = I_1 \left(V_{CC} - \frac{V_P}{2} \right)$$

The average power consumed by I_1 is

$$P_{I_1} = -I_1 V_{EE} = I_1 V_{CC}$$
 with $V_{EE} = -V_{CC}$

Thus the total average circuit power is

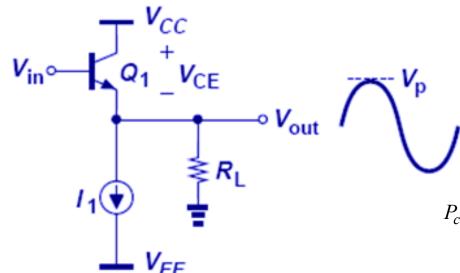
$$P_{ckt} = I_1 \left(V_{CC} - \frac{V_P}{2} \right) + I_1 V_{CC} = I_1 \left(2V_{CC} - \frac{V_P}{2} \right)$$

- The Emitter Follower Efficiency is $\eta_{EF} = \frac{\frac{V_P^2}{2R_L}}{\frac{V_P^2}{2R_L} + I_1 \left(2V_{CC} \frac{V_P}{2}\right)}$ The emitter follower out stage only has a peak efficiency of 25% as V_P goes to V_{CC}
 - with $I_1 = \frac{V_P}{R_L}$ \Rightarrow $\eta_{EF} = \frac{V_P}{4V_{CC}}$

- The emitter follower output
- Note, this can't actually be achieved, as we need some V_{CF} and voltage across I₁

Emitter Follower Efficiency Example

• What if the emitter follower is designed to deliver V_p , but only operates with $V_p = V_{CC}/2$?



Now the average power delivered to the load is

$$P_{out} = \frac{\left(\frac{V_P}{2}\right)^2}{2R_L} = \frac{V_P^2}{8R_L}$$

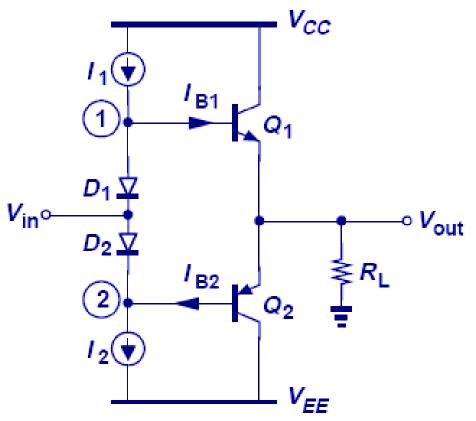
The total average circuit power becomes

$$P_{ckt} = I_1 \left(2V_{CC} - \frac{V_P}{4} \right) = \frac{2V_P^2}{R_L} - \frac{V_P^2}{4R_L} \text{ with } I_1 = \frac{V_P}{R_L} \text{ and } V_{CC} = V_P$$

$$\eta_{EF} = \frac{\frac{V_P^2}{8R_L}}{\frac{V_P^2}{8R_L} + \frac{2V_P^2}{R_L} - \frac{V_P^2}{4R_L}} = \frac{1}{15}$$

Now the efficiency drops to only 6.7%

Push-Pull Stage Efficiency



The average power delivered to the load is

$$P_{out} = \frac{V_P^2}{2R_L}$$

Both Q_1 and Q_2 consume an average power of

$$P_{Q_{1,2}} = \frac{V_P}{R_L} \left(\frac{V_{CC}}{\pi} - \frac{V_P}{4} \right)$$

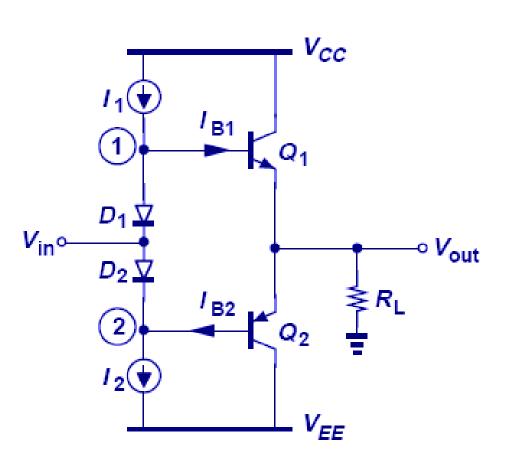
- The push-pull output stage has a peak efficiency of 78.5% as V_P goes to V_{CC}
- Also, we are excluding the input bias stage

The Push - Pull Stage Efficiency is $\eta_{PP} = \frac{\frac{V_P}{2R_L}}{\frac{V_P^2}{2R_L} + \frac{2V_P}{R} \left(\frac{V_{CC}}{\pi} - \frac{V_P}{4} \right)}$ Note, uns can caccam, achieved, as we need some V_{CE} across both V_{CE} and V_{CE} across both V_{CE} and V_{CE} across both V_{CE} and V_{CE}

$$\eta_{PP} = \frac{\pi V_P}{4V_{CC}}$$

Total Push-Pull Stage Efficiency

 Assume that I₁=I₂ and that they are chosen to allow a peak swing of V_P



In order to support a peak swing of V_P

$$I_1 = \frac{V_P}{\beta R_L}$$

The input bias stage power is

$$\frac{2V_{CC}V_P}{\beta R_L}$$

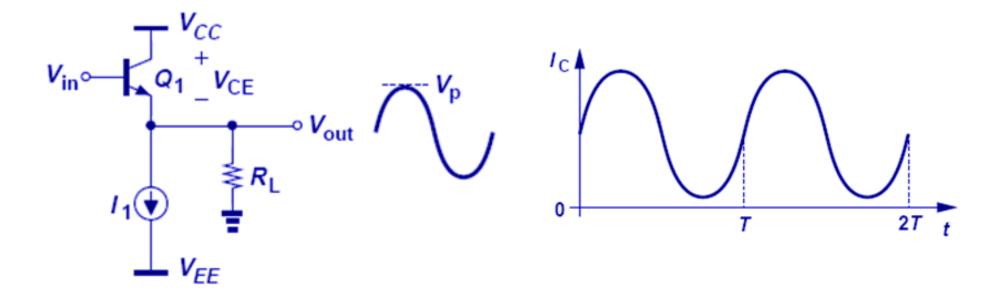
Thus the total push - pull stage efficiency is

$$\eta_{PP} = \frac{\frac{V_{P}^{2}}{2R_{L}}}{\frac{2V_{P}V_{CC}}{\pi R_{L}} + \frac{2V_{CC}V_{P}}{\beta R_{L}}}$$

$$\eta_{PP} = \frac{1}{4} \left(\frac{V_P}{\frac{V_{CC}}{\pi} + \frac{V_P}{\beta}} \right)$$

Class A Power Amplifiers

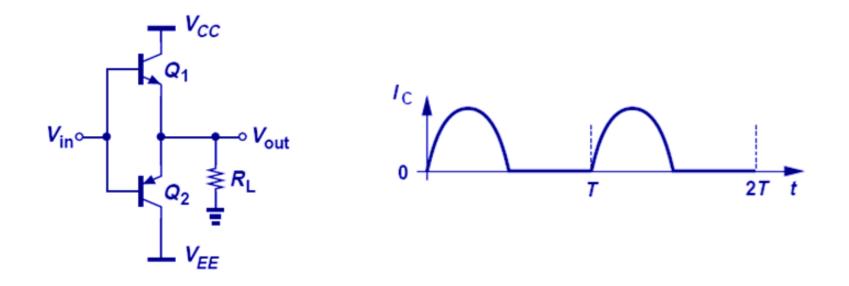
- Each transistor is on for the entire cycle
- Emitter follower is a Class A power amplifier



 Display high linearity, but low efficiency (25% maximum)

Class B Power Amplifiers

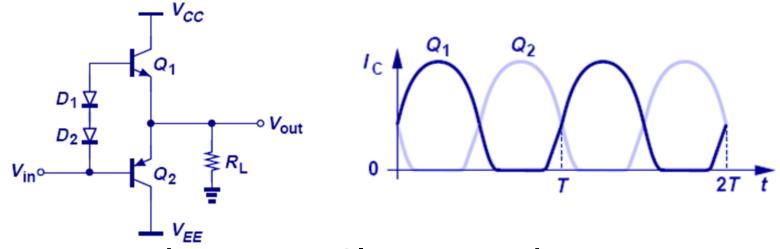
- Each transistor conducts for half the cycle
- Simple push-pull stage is a Class B power amp



- Display high efficiency, but low linearity
 - Bad crossover distortion

Class AB Power Amplifiers

- Each transistor conducts for slightly more than a half-cycle
- Improved push-pull stage is a Class AB power amp



- Compromise between Class A and B
 - Good distortion at slightly degraded efficiency
- Many other PA classes exist (C, D, E, ...) and are often studied in grad-level RF circuit design classes

Thanks for the fun semester!!!